CSD18504Q5A 40-V N-Channel NexFET™ Power MOSFET

1 Features

- Ultra-Low Q_g and Q_{gd}
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5 mm × 6 mm Plastic Package

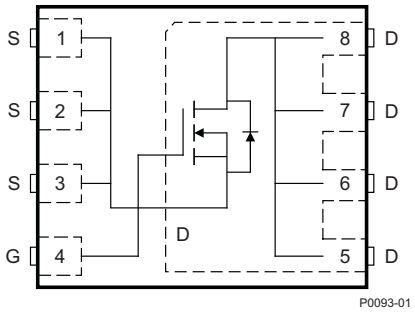
2 Applications

- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Battery Motor Control

3 Description

This 5.3 mΩ, SON 5 × 6 mm, 40 V NexFET™ power MOSFET is designed to minimize losses in power conversion applications.

Top View



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Product Summary

T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	40		V
Q_g	Gate Charge Total (4.5 V)	7.7		nC
Q_{gd}	Gate Charge Gate-to-Drain	2.4		nC
$R_{DS(on)}$	Drain-to-Source On-Resistance	V_{GS} = 4.5 V	7.5	mΩ
		V_{GS} = 10 V	5.3	mΩ
$V_{GS(th)}$	Threshold Voltage	1.9		V

Ordering Information(1)

Device	Qty	Media	Package	Ship
CSD18504Q5A	2500	13-Inch Reel	SON 5 mm × 6 mm Plastic Package	Tape and Reel
CSD18504Q5AT	250	7-Inch Reel		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

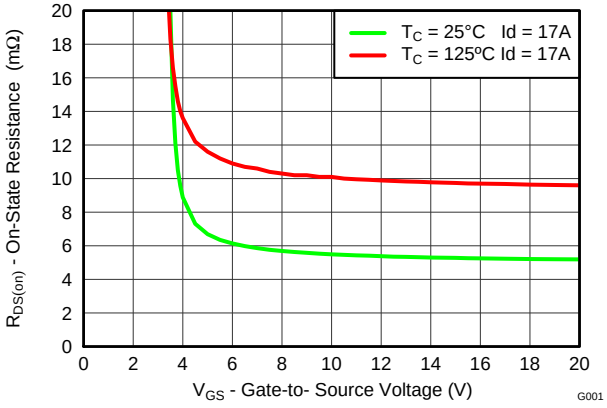
Absolute Maximum Ratings

T_A = 25°C		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	40	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current (Package limited)	50	A
	Continuous Drain Current (Silicon limited), T_C = 25°C	75	
	Continuous Drain Current(1)	15	
I_{DM}	Pulsed Drain Current(2)	275	A
P_D	Power Dissipation(1)	3.1	W
	Power Dissipation, T_C = 25°C	77	
T_J, T_{stg}	Operating Junction and Storage Temperature Range	–55 to 150	°C
E_{AS}	Avalanche Energy, single pulse I_D = 43 A, L = 0.1 mH, R_G = 25 Ω	92	mJ

(1) Typical $R_{\theta JA}$ = 40°C/W on a 1-inch^2 , 2-oz. Cu pad on a 0.06-inch thick FR4 PCB.

(2) Max $R_{\theta JC}$ = 2.0 °C/W, pulse duration ≤100 µs, duty cycle ≤1%

$R_{DS(on)}$ vs V_{GS}



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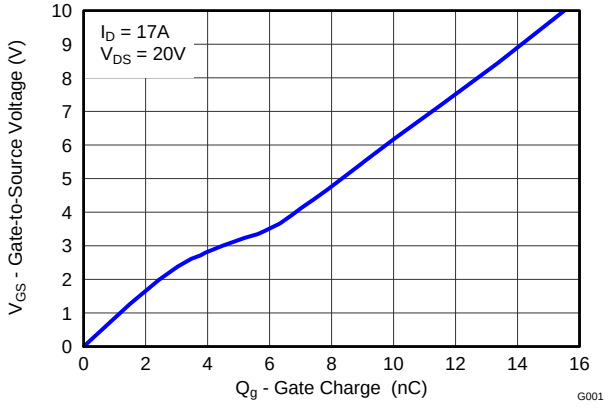
Gate Charge



G001

Table of Contents

4 Revision History

Changes from Revision D (August 2014) to Revision E — **Page**

- Increased pulsed current to 275 A ... 1
- Updated the SOA in Figure 10 ... 6

Changes from Revision C (May 2013) to Revision D — **Page**

- Added 7-inch reel to Ordering Information table ... 1
- Added parameter for power dissipation with case temperature held to 25°C ... 1
- Updated pulsed current conditions ... 1
- Updated Figure 1 to a normalized $R_{\theta JC}$ curve ... 4

Changes from Revision B (November 2012) to Revision C — **Page**

- Updated this drawing table to include E3, e1, and e2 dimensions ... 8
- Added Stencil Pattern ... 10

Changes from Revision A (October 2012) to Revision B — **Page**

- Changed the $R_{DS(on)}$ vs V_{GS} and Gate Charger graphs ... 1
- Changed $R_{\theta JA}$ Max value From: 51 To: 50°C/W ... 3
- Changed the Typical MOSFET Characteristics section ... 4

Changes from Original (June 2012) to Revision A — **Page**

- Changed the Transconductance TYP value From: 63 S To: 71 S ... 3
- Changed the Turn On and Turn Off Delay Time, Rise and Fall Time Test Conditions From: I_{DS} = 17 A, R_G = 2 Ω To: I_{DS} = 17 A, R_G = 0 Ω ... 3
- Changed the Q_{rr} Reverse Recovery Charge TYP value From: 18 nC To: 39 nC ... 3

5 Specifications

5.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

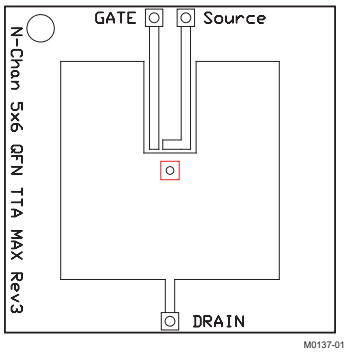
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-Source Voltage	V_{GS} = 0 V, I_D = 250 µA	40			V
I_{DSS}	Drain-to-Source Leakage Current	V_{GS} = 0 V, V_{DS} = 32 V			1	µA
I_{GSS}	Gate-to-Source Leakage Current	V_{DS} = 0 V, V_{GS} = 20 V			100	nA
$V_{GS(th)}$	Gate-to-Source Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	1.5	1.9	2.4	V
$R_{DS(on)}$	Drain-to-Source On-Resistance	V_{GS} = 4.5 V, I_D = 17 A		7.5	9.8	mΩ
		V_{GS} = 10 V, I_D = 17 A		5.3	6.6	mΩ
g_{fs}	Transconductance	V_{DS} = 20 V, I_D = 17 A		71		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{GS} = 0 V, V_{DS} = 20 V, f = 1 MHz		1380	1656	pF
C_{oss}	Output Capacitance			310	372	pF
C_{rss}	Reverse Transfer Capacitance			8	9.6	pF
R_G	Series Gate Resistance			1.4	2.8	Ω
Q_g	Gate Charge Total (4.5 V)	V_{DS} = 20 V, I_D = 17 A		7.7	9.2	nC
Q_g	Gate Charge Total (10 V)			16	19	
Q_{gd}	Gate Charge Gate-to-Drain			2.4		nC
Q_{gs}	Gate Charge Gate-to-Source			3.2		nC
$Q_{g(th)}$	Gate Charge at V_{th}			2.2		nC
Q_{oss}	Output Charge	V_{DS} = 20 V, V_{GS} = 0 V		21		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = 20 V, V_{GS} = 10 V, I_{DS} = 17 A, R_G = 0 Ω		3.2		ns
t_r	Rise Time			6.8		ns
$t_{d(off)}$	Turn Off Delay Time			12		ns
t_f	Fall Time			2		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode Forward Voltage	I_{SD} = 17 A, V_{GS} = 0 V		0.8	1	V
Q_{rr}	Reverse Recovery Charge	V_{DS}= 20 V, I_F = 17 A, di/dt = 300 A/µs		39		nC
t_{rr}	Reverse Recovery Time			28		ns

5.2 Thermal Information

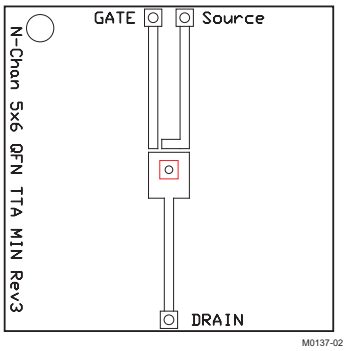
(T_A = 25°C unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance(1)			2.0	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance(1)(2)			50	

(1) $R_{\theta JC}$ is determined with the device mounted on a 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inches × 1.5-inches (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1-inch^2 (6.45-cm^2), 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 50°C/W when mounted on 1 inch^2 (6.45 cm^2) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA}$ = 125°C/W when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

5.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)

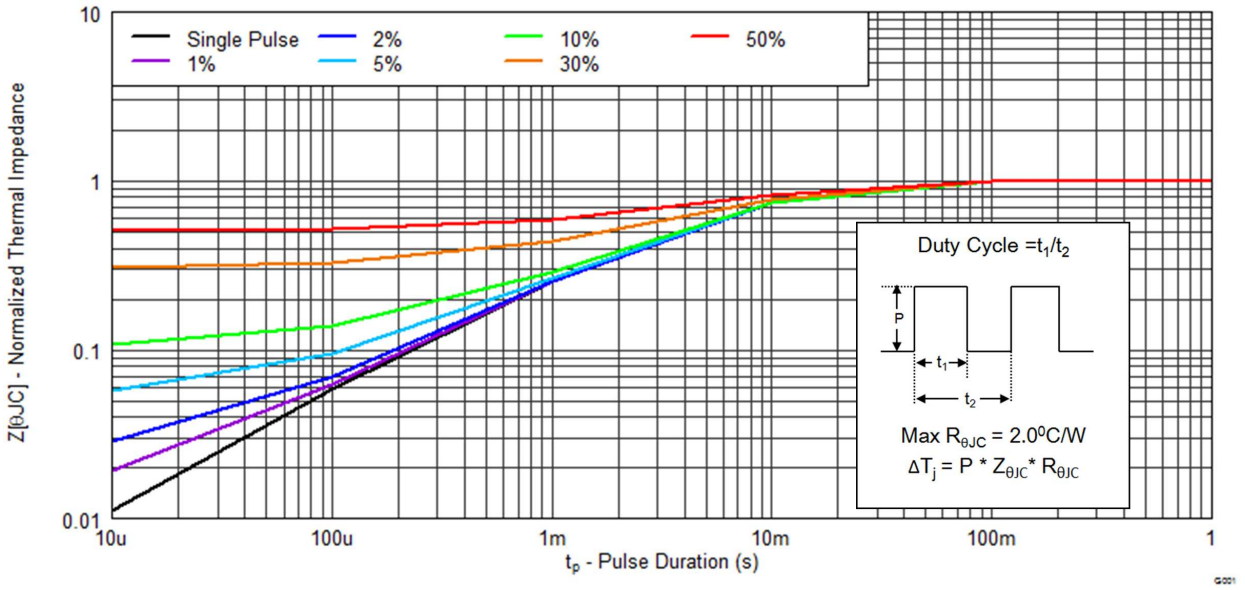


Figure 1. Transient Thermal Impedance

Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

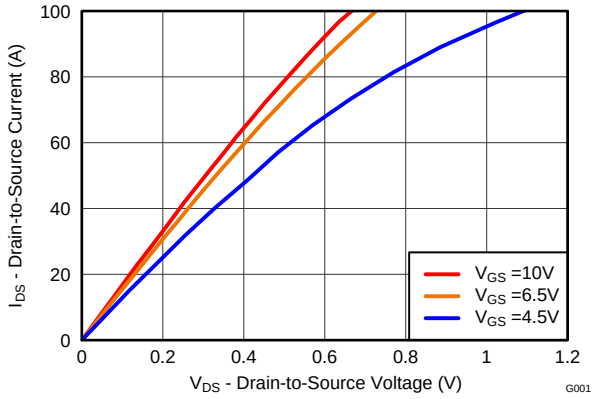


Figure 2. Saturation Characteristics

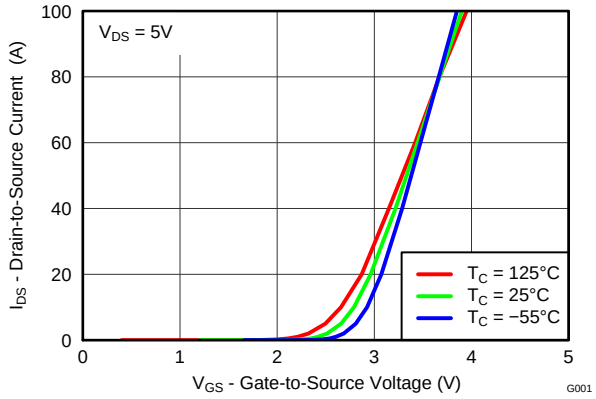


Figure 3. Transfer Characteristics

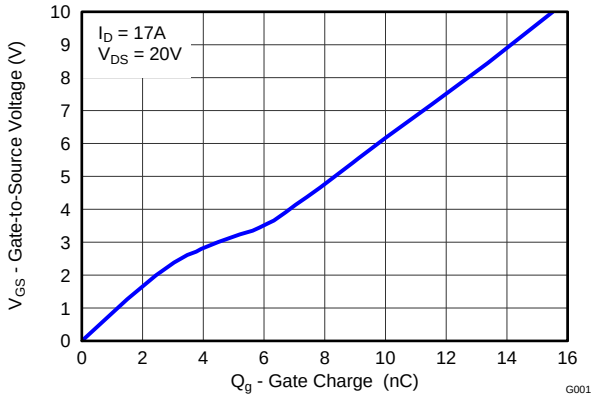


Figure 4. Gate Charge

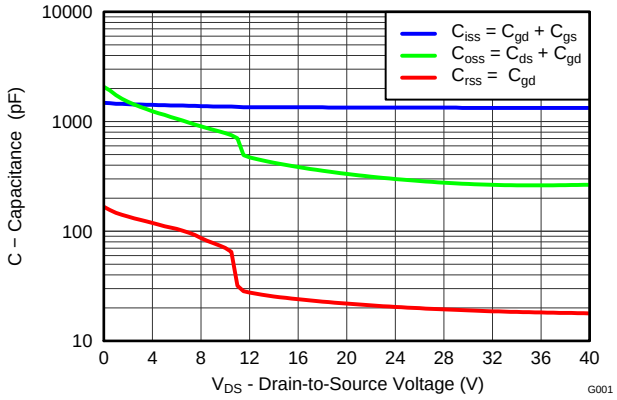


Figure 5. Capacitance

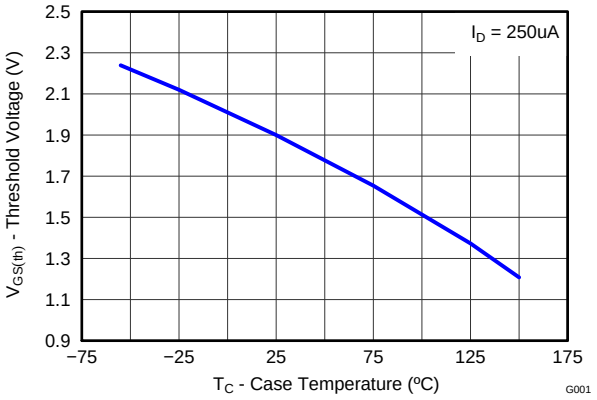


Figure 6. Threshold Voltage vs Temperature

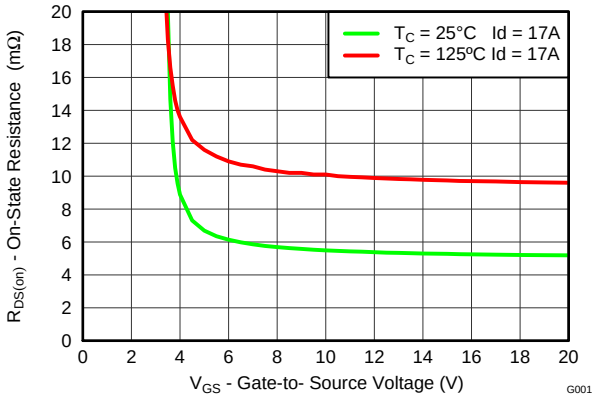


Figure 7. On-State Resistance vs Gate-to-Source Voltage

Typical MOSFET Characteristics (continued)

(T_A = 25°C unless otherwise stated)

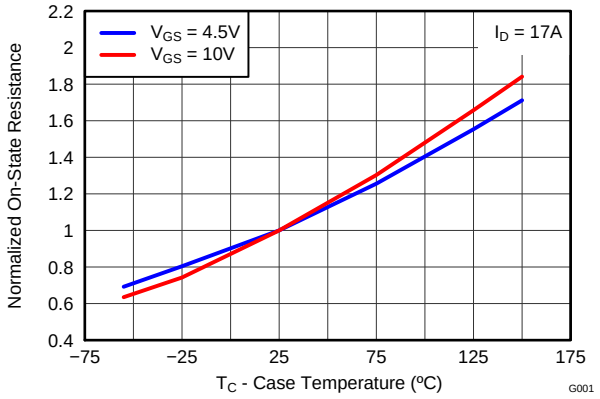


Figure 8. Normalized On-State Resistance vs Temperature

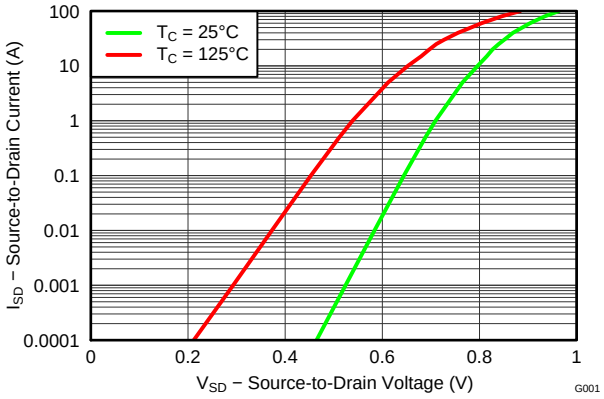


Figure 9. Typical Diode Forward Voltage

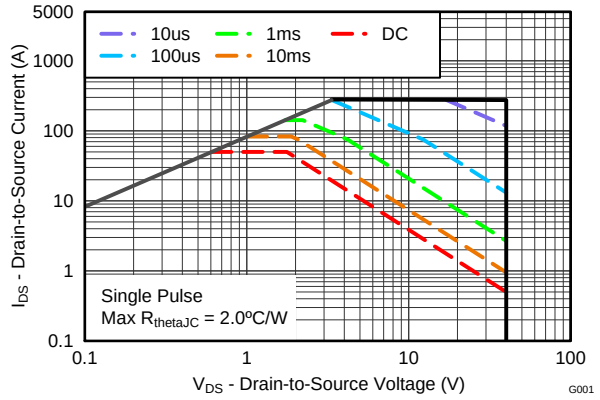


Figure 10. Maximum Safe Operating Area

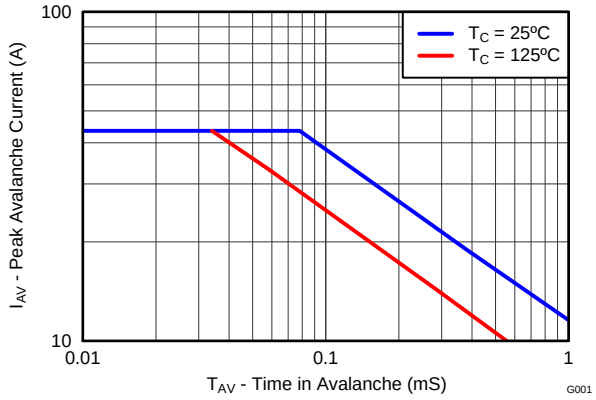


Figure 11. Single Pulse Unclamped Inductive Switching

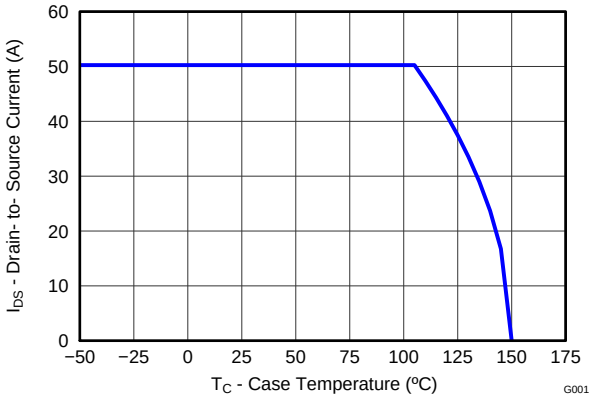


Figure 12. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Trademarks

NexFET is a trademark of Texas Instruments.

6.2 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.3 Glossary

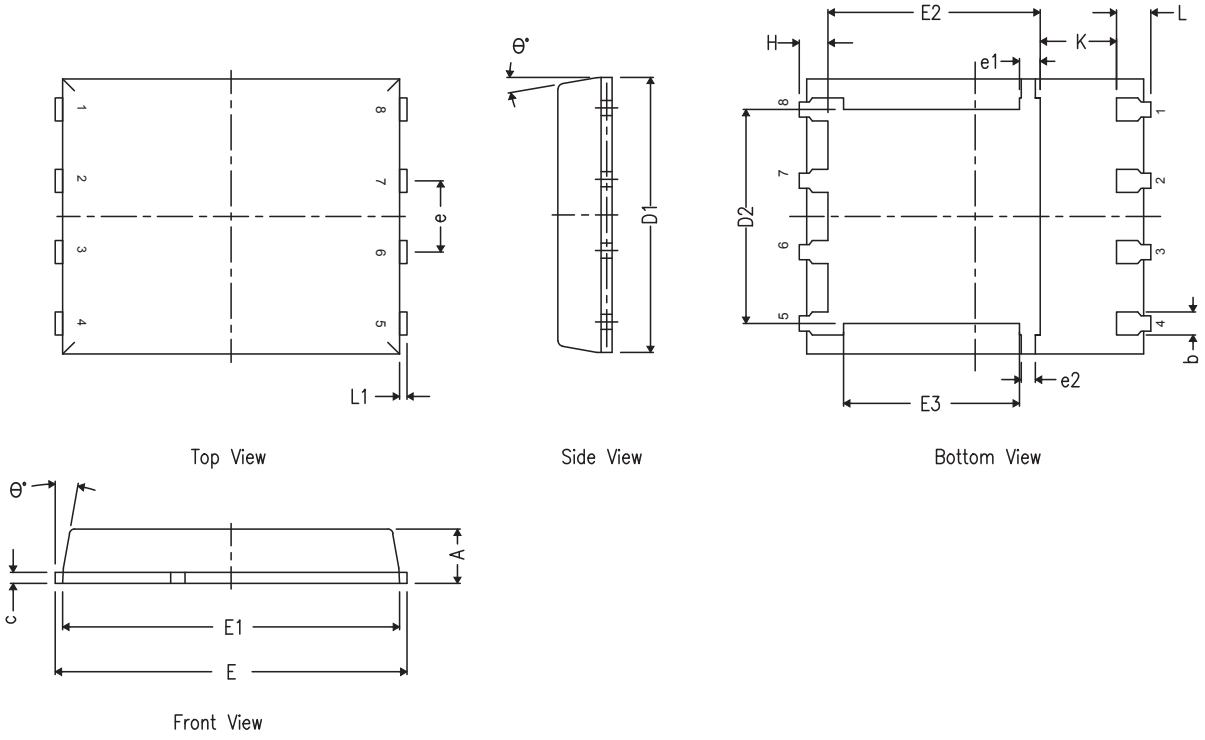
SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 Mechanical, Packaging, and Orderable Information

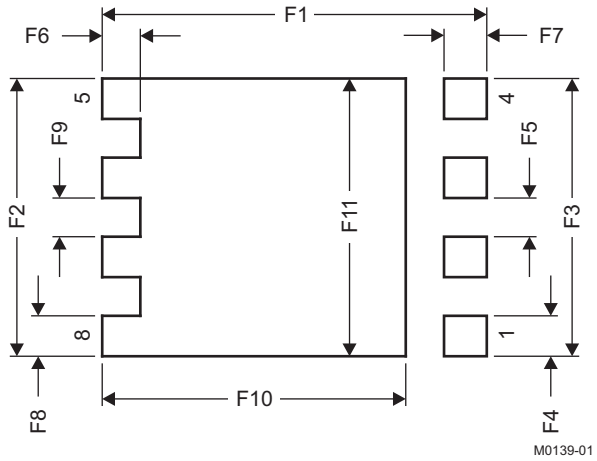
The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Q5A Package Dimensions



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.33	0.41	0.51
c	0.20	0.25	0.34
D1	4.80	4.90	5.00
D2	3.61	3.81	4.02
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
E3	3.03	3.13	3.23
e	1.17	1.27	1.37
e1	0.27	0.37	0.47
e2	0.15	0.25	0.35
H	0.41	0.56	0.71
K	1.10	—	—
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
θ	0°	—	12°

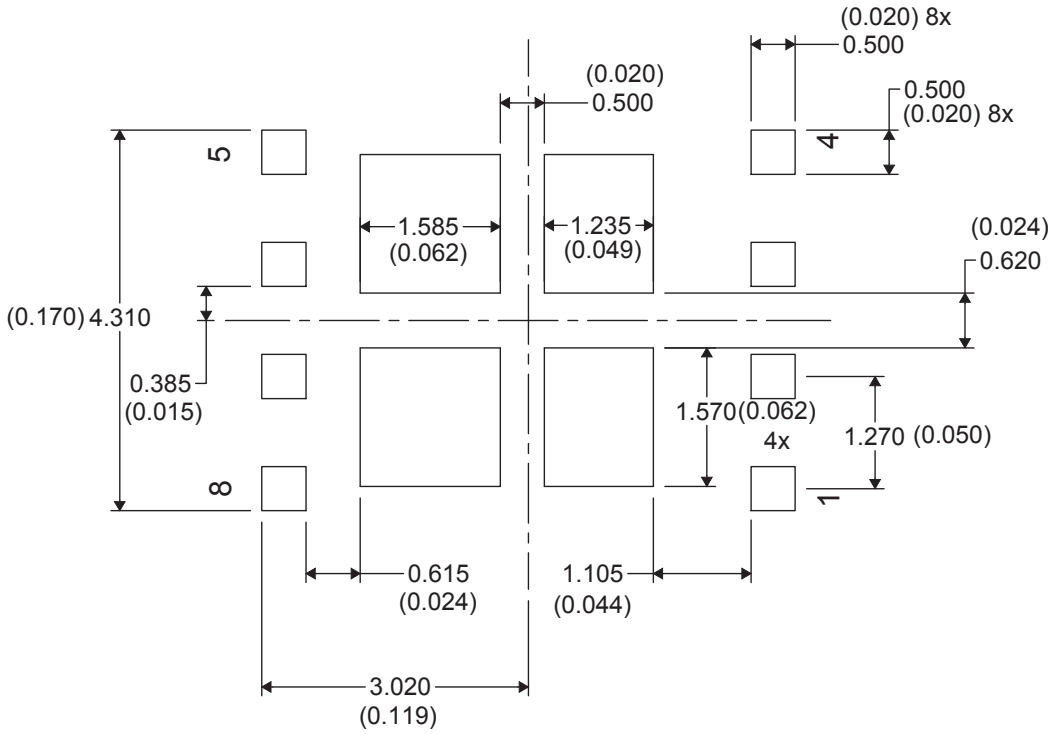
7.2 Recommended PCB Pattern



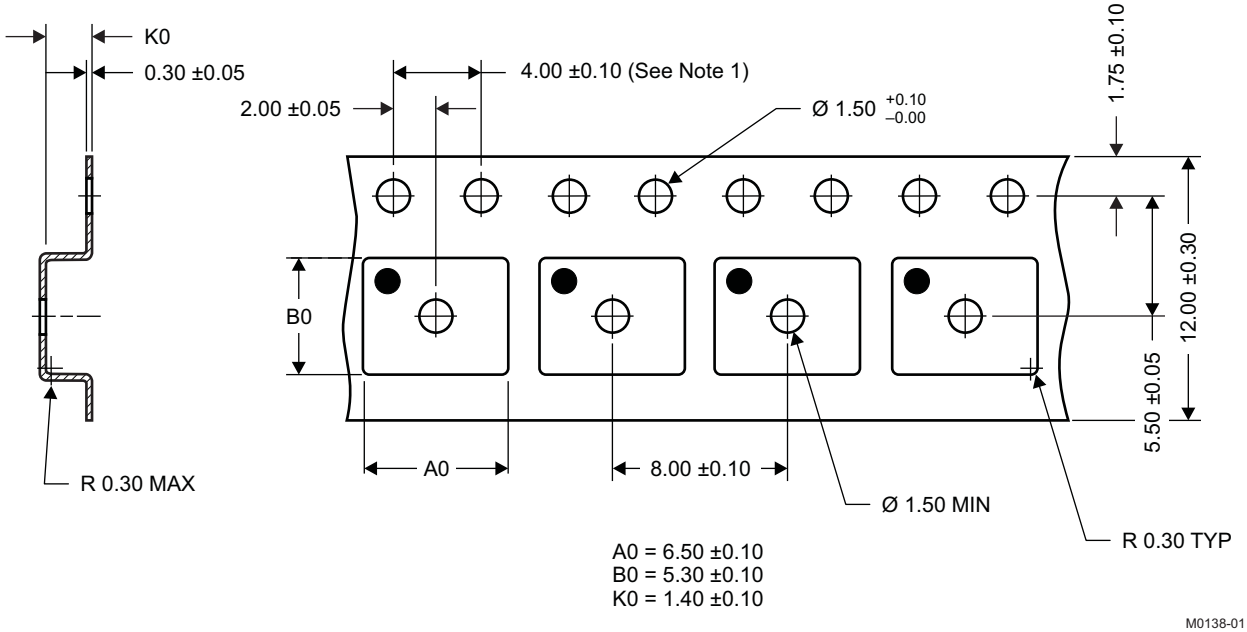
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.46	4.56	0.176	0.18
F3	4.46	4.56	0.176	0.18
F4	0.65	0.7	0.026	0.028
F5	0.62	0.67	0.024	0.026
F6	0.63	0.68	0.025	0.027
F7	0.7	0.8	0.028	0.031
F8	0.65	0.7	0.026	0.028
F9	0.62	0.67	0.024	0.026
F10	4.9	5	0.193	0.197
F11	4.46	4.56	0.176	0.18

For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

7.3 Recommended Stencil Opening



7.4 Q5A Tape and Reel Information



Notes:

1. 10-sprocket hole-pitch cumulative tolerance ±0.2
2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
3. Material: black static-dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified).
5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD18504Q5A	ACTIVE	VSONP	DQJ	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18504	Samples
CSD18504Q5AT	ACTIVE	VSONP	DQJ	8	250	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD18504	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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RFID	www.ti-rfid.com		
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